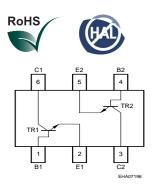


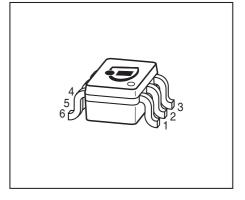
### Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain broadband amplifiers at collector currents from 0.5 mA to 12 mA
- $f_{\rm T}$  = 8 GHz,  $NF_{\rm min}$  = 0.9 dB at 900 MHz
- Two (galvanic) internal isolated Transistors in one package
- For orientation in reel see package information below
- Easy to use Pb-free (RoHS compliant) and halogen free industry standard package with visible leads
- Qualification report according to AEC-Q101 available



**ESD** (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration					Package	
BFS481	RFs	1=B	2=E	3=C	4=B	5=E	6=C	SOT363



## **BFS481**



Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V <sub>CEO</sub>	12	V	
Collector-emitter voltage	V <sub>CES</sub>	20		
Collector-base voltage	V <sub>CBO</sub>	20		
Emitter-base voltage	V <sub>EBO</sub>	2		
Collector current	I <sub>C</sub>	20	mA	
Base current	I <sub>B</sub>	2		
Total power dissipation <sup>1)</sup>	P <sub>tot</sub>	175	mW	
<i>T</i> <sub>S</sub> ≤ 83 °C				
Junction temperature	TJ	150	°C	
Storage temperature	T <sub>Stg</sub>	-55 150		

#### **Maximum Ratings** at $T_A = 25$ °C, unless otherwise specified

#### **Thermal Resistance**

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>2)</sup>	R <sub>thJS</sub>	380	K/W

## **Electrical Characteristics** at $T_A$ = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					-
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	12	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	100	μA
$V_{\rm CE}$ = 20 V, $V_{\rm BE}$ = 0					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB} = 10  \text{V},  I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	-	1	μA
$V_{\rm EB}$ = 1 V, $I_{\rm C}$ = 0					
DC current gain	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, pulse measured					

 ${}^{1}T_{S}$  is measured on the collector lead at the soldering point of the pcb

<sup>2</sup>For the definition of  $R_{\text{thJS}}$  please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol		Unit			
		min.	typ.	max.		
AC Characteristics (verified by random sampling)						
Transition frequency	f <sub>T</sub>	6	8	-	GHz	
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $f$ = 500 MHz						
Collector-base capacitance	C <sub>cb</sub>	-	0.23	0.4	pF	
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,						
emitter grounded						
Collector emitter capacitance	C <sub>ce</sub>	-	0.13	-		
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,						
base grounded						
Emitter-base capacitance	C <sub>eb</sub>	-	0.4	-		
V <sub>EB</sub> = 0.5 V, <i>f</i> = 1 MHz, V <sub>CB</sub> = 0 ,						
collector grounded						
Minimum noise figure	NF <sub>min</sub>				dB	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,						
<i>f</i> = 900 MHz		-	0.9	-		
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,						
<i>f</i> = 1.8 GHz		-	1.2	-		
Power gain, maximum stable <sup>1)</sup>	G <sub>ms</sub>	-	20	-	dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,						
<i>f</i> = 900 MHz						
Power gain, maximum available <sup>2)</sup>	G <sub>ma</sub>	-	15	-	dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ , $Z_{\rm L}$ = $Z_{\rm Lopt}$ ,						
<i>f</i> = 1.8 GHz						
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB	
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω,						
<i>f</i> = 900 MHz		-	16	-		
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,						
<i>f</i> = 1.8 MHz		-	11	-		

# **Electrical Characteristics** at $T_A = 25$ °C, unless otherwise specified

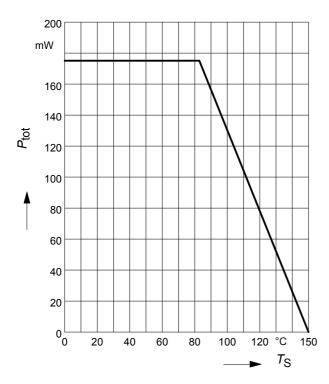
 ${}^{1}G_{\rm ms} = |S_{21} / S_{12}|$  ${}^{2}G_{\rm ma} = |S_{21e} / S_{12e}| \ (k - (k^2 - 1)^{1/2})$ 



**BFS481** 

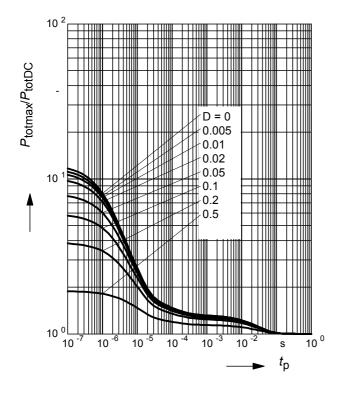
# Total power dissipation $P_{tot} = f(T_S)$

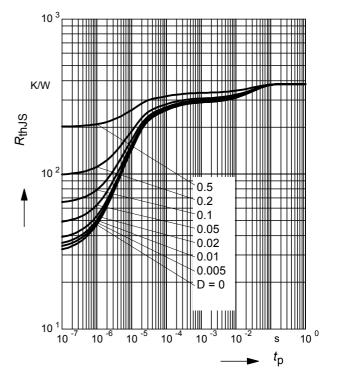
**Permissible Pulse Load**  $R_{\text{thJS}} = f(t_p)$ 



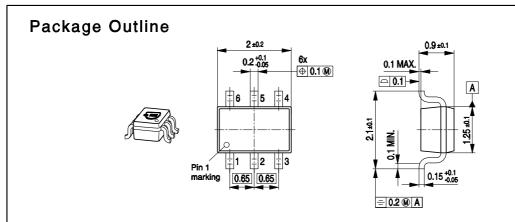
# Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$ 

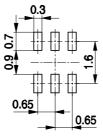






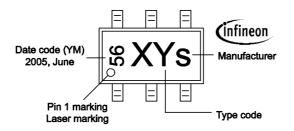


## **Foot Print**



# Marking Layout (Example)

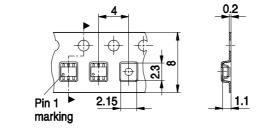
Small variations in positioning of Date code, Type code and Manufacture are possible.



### Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.







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